Fei Xue

List of Publications by Year
in descending order

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33	704	17	26
papers	citations	h-index	g-index

471061 552369

33	33	33	659
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Effects of barrier layers on device performance of high mobility In0.7Ga0.3As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2010, 96, .	1.5	66
2	Electroforming and resistive switching in silicon dioxide resistive memory devices. RSC Advances, 2015, 5, 21215-21236.	1.7	59
3	Sub-50-nm $hbox{In}_{0.7}hbox{Ga}_{0.3}hbox{As}$ MOSFETs With Various Barrier Layer Materials. IEEE Electron Device Letters, 2012, 33, 32-34.	2.2	51
4	Memory switching properties of e-beam evaporated SiOx on N++ Si substrate. Applied Physics Letters, 2012, 100, .	1.5	48
5	Study of polarity effect in SiO_x-based resistive switching memory. Applied Physics Letters, 2012, 101, 052111.	1.5	47
6	Effects of gate-first and gate-last process on interface quality of In0.53Ga0.47As metal-oxide-semiconductor capacitors using atomic-layer-deposited Al2O3 and HfO2 oxides. Applied Physics Letters, 2009, 95, .	1.5	42
7	InAs inserted InGaAs buried channel metal-oxide-semiconductor field-effect-transistors with atomic-layer-deposited gate dielectric. Applied Physics Letters, 2011, 98, .	1.5	36
8	Improved electrical characteristics of TaN/Al2O3/In0.53Ga0.47As metal-oxide-semiconductor field-effect transistors by fluorine incorporation. Applied Physics Letters, 2009, 95, 013501.	1.5	33
9	Oxygen-induced bi-modal failure phenomenon in SiOx-based resistive switching memory. Applied Physics Letters, 2013, 103, 033521.	1.5	30
10	Improving the on-current of In0.7Ga0.3As tunneling field-effect-transistors by p++/n+ tunneling junction. Applied Physics Letters, 2011, 98, .	1.5	26
11	Investigation of edge- and bulk-related resistive switching behaviors and backward-scan effects in SiO_x-based resistive switching memory. Applied Physics Letters, 2013, 103, 193508.	1.5	26
12	Tristate Operation in Resistive Switching of $ hbox{SiO}_{2}$ Thin Films. IEEE Electron Device Letters, 2012, 33, 1702-1704.	2.2	25
13	Fluorinated HfO2 gate dielectric engineering on In0.53Ga0.47As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2010, 96, .	1.5	24
14	Effects of fluorine incorporation into HfO2 gate dielectrics on InP and In0.53Ga0.47As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2010, 96, 253502.	1.5	24
15	Effect of hydrogen/deuterium incorporation on electroforming voltage of SiOx resistive random access memory. Applied Physics Letters, 2012, 101, .	1.5	20
16	Effects of sidewall etching on electrical properties of SiOx resistive random access memory. Applied Physics Letters, 2013, 103, 213505.	1.5	20
17	High-k InGaAs metal-oxide-semiconductor field-effect-transistors with various barrier layer materials. Applied Physics Letters, 2011, 99, 033507.	1.5	19
18	Nonplanar InGaAs Gate Wrapped Around Field-Effect Transistors. IEEE Transactions on Electron Devices, 2014, 61, 2332-2337.	1.6	16

#	Article	IF	Citations
19	Physical and Electrical Analysis of Post-$ hbox{HfO}_{2}$ Fluorine Plasma Treatment for the Improvement of $hbox{In}_{0.53}hbox{Ga}_{0.47}hbox{As}$ MOSFETs' Performance. IEEE Transactions on Electron Devices, 2012, 59, 139-144.	1.6	13
20	Impact of SF6 plasma treatment on performance of TaNâ€"HfO2â€"InP metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2011, 98, 043506.	1.5	10
21	Channel Thickness Dependence of InGaAs Quantum-Well Field-Effect Transistors With High- $kappa$ Gate Dielectrics. IEEE Electron Device Letters, 2012, 33, 1255-1257.	2.2	10
22	Study of SiO<inf>x</inf>-based complementary resistive switching memristor. , 2012, , .		9
23	Comprehensive trap-level study in SiO<inf>x</inf>-based resistive switching memory. , 2013, , .		9
24	Excellent device performance of 3D In<inf>0.53</inf>Ga<inf>0.47</inf>As gate-wrap-around field-effect-transistors with high-k gate dielectrics. , 2012, , .		8
25	HfO2 dielectrics engineering using low power SF6 plasma on InP and In0.53Ga0.47As metal-oxide-semiconductor field-effect-transistors. Applied Physics Letters, 2012, 100, 243508.	1.5	6
26	Optimization of Fluorine Plasma Treatment for Interface Improvement on HfO2/In0.53Ga0.47As MOSFETs. Applied Sciences (Switzerland), 2012, 2, 233-244.	1.3	6
27	Investigation of Surface Channel InGaAs MOSFETs with Al₂O₃ and ZrO₂ ALD Gate Dielectric. ECS Transactions, 2010, 33, 479-485.	0.3	5
28	Effects of InP barrier layer thicknesses and different ALD oxides on device performance of In<inf>0.7</inf>Ga<inf>0.3</inf>As MOSFETs. , 2010, , .		5
29	Effect of indium concentration on InGaAs channel metal-oxide-semiconductor field-effect transistors with atomic layer deposited gate dielectric. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	3
30	III-V Gate-wrap-around field-effect-transistors with high-k gate dielectrics. , 2014, , .		3
31	Effects of SF₆ plasma treatment on electrical characteristics of TaN-Al₂O₃-InP metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2012, 101, 063505.	1.5	2
32	Resistive switching characteristics and mechanisms in silicon oxide memory devices. ChemistrySelect, 2016, 1, .	0.7	2
33	In0.7Ga0.3 as Tunneling Field-Effect-Transistors with LaAlO3 and ZrO2 High-k Dielectrics. ECS Transactions, 2011, 41, 249-253.	0.3	1